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International
IOR Rectifier

AUTOMOTIVE GRADE

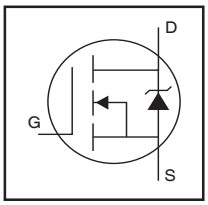
PD - 97741

AUIRF3205

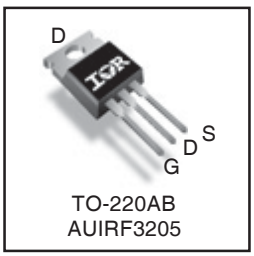
HEXFET® Power MOSFET

Features

- Advanced Planar Technology
- Low On-Resistance
- Dynamic dV/dT Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified*



$V_{(BR)DSS}$	55V
$R_{DS(on)}$ max.	8.0mΩ
I_D (Silicon Limited)	110A⑤
I_D (Package Limited)	75A



TO-220AB
AUIRF3205

G	D	S
Gate	Drain	Source

Description

Specifically designed for Automotive applications, this Stripe Planar design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V (Silicon Limited)	110⑤	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V (Silicon Limited)	80⑤	
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V (Package Limited)	75	
I_{DM}	Pulsed Drain Current ①	390	
P_D @T_C = 25°C	Power Dissipation	200	W
	Linear Derating Factor	1.3	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy (Thermally Limited)②	264⑦	mJ
I_{AR}	Avalanche Current ①	62	A
E_{AR}	Repetitive Avalanche Energy ①⑥	20	mJ
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting Torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑧	—	0.75	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient	—	62	

HEXFET® is a registered trademark of International Rectifier.
*Qualification standards can be found at http://www.irf.com/

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Static Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	55	—	—	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.057	—	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	8.0	mΩ	V_{GS} = 10V, I_D = 62A ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	V_{DS} = V_{GS}, I_D = 250µA
gfs	Forward Transconductance	44	—	—	S	V_{DS} = 25V, I_D = 62A ④
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	µA	V_{DS} = 55V, V_{GS} = 0V
		—	—	250		V_{DS} = 44V, V_{GS} = 0V, T_J = 150°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V_{GS} = -20V

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge	—	—	146	nC	I_D = 62A
Q_{gs}	Gate-to-Source Charge	—	—	35		V_{DS} = 44V
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	54		V_{GS} = 10V, See Fig. 6 & 13 ④
$t_{d(on)}$	Turn-On Delay Time	—	14	—	ns	V_{DD} = 28V
t_r	Rise Time	—	101	—		I_D = 62A
$t_{d(off)}$	Turn-Off Delay Time	—	50	—		R_G = 4.5 Ω
t_f	Fall Time	—	65	—		V_{GS} = 10V, See Fig. 10 ④
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	3247	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	781	—		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	—	211	—		f = 1.0MHz, See Fig. 5

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	110	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	390		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	T_J = 25°C, I_S = 62A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	—	69	104	ns	T_J = 25°C, I_F = 62A
Q_{rr}	Reverse Recovery Charge	—	143	215	nC	di/dt = 100A/µs ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② Starting T_J = 25°C, L = 138µH, R_G = 25Ω, I_{AS} = 62A. (See Figure 12)

③ I_{SD} ≤ 62A, di/dt ≤ 207A/µs, V_{DD} ≤ $V_{(BR)DSS}$, T_J ≤ 175°C.

④ Pulse width ≤ 400µs; duty cycle ≤ 2%.

⑤ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75A.

⑥ This is a typical value at device destruction and represents operation outside rated limits.

⑦ This is a calculated value limited to T_J = 175°C.

⑧ R_θ is measured at T_J of approximately 90°C.

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Qualification Information†

Qualification Level		Automotive (per AEC-Q101) ††	
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		TO-220	N/A
ESD	Machine Model	Class M4 (+/- 600V)††† AEC-Q101-002	
	Human Body Model	Class H1C (+/- 2000V)††† AEC-Q101-001	
	Charged Device Model	Class C5 (+/- 2000V)††† AEC-Q101-005	
RoHS Compliant		Yes	

† Qualification standards can be found at International Rectifier's web site: http//www.irf.com/

†† Exceptions (if any) to AEC-Q101 requirements are noted in the qualification report.

††† Highest passing voltage.

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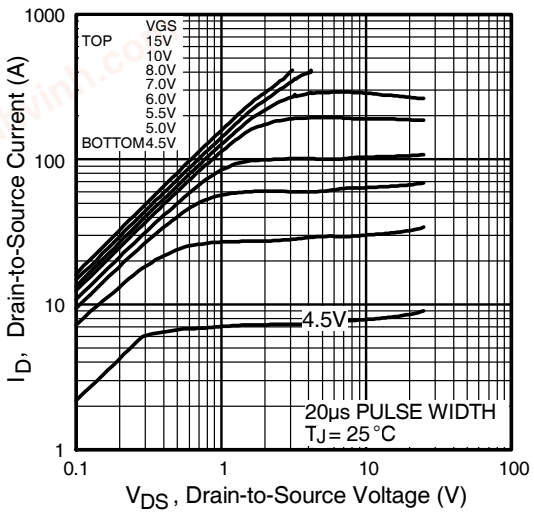


Fig 1. Typical Output Characteristics

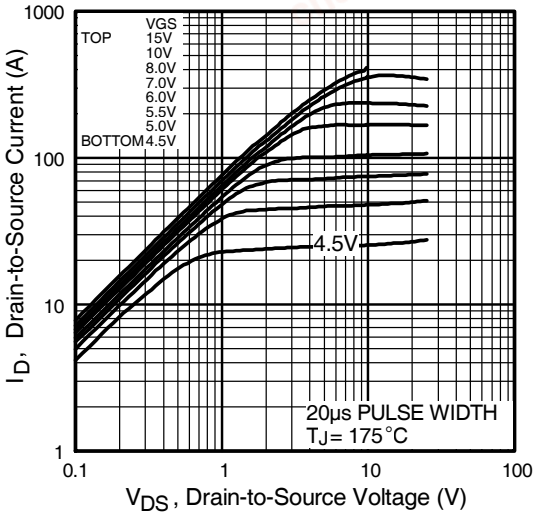


Fig 2. Typical Output Characteristics

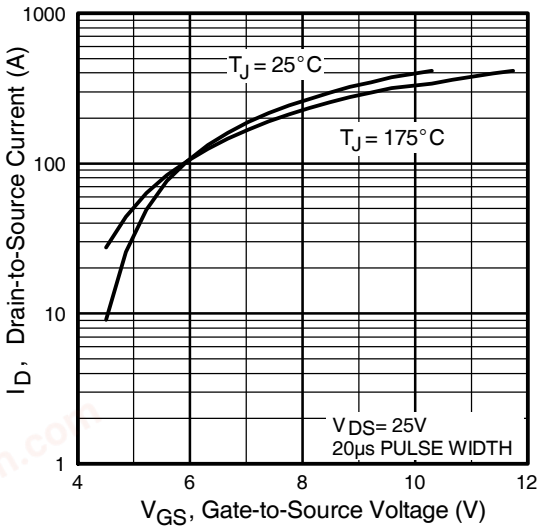


Fig 3. Typical Transfer Characteristics

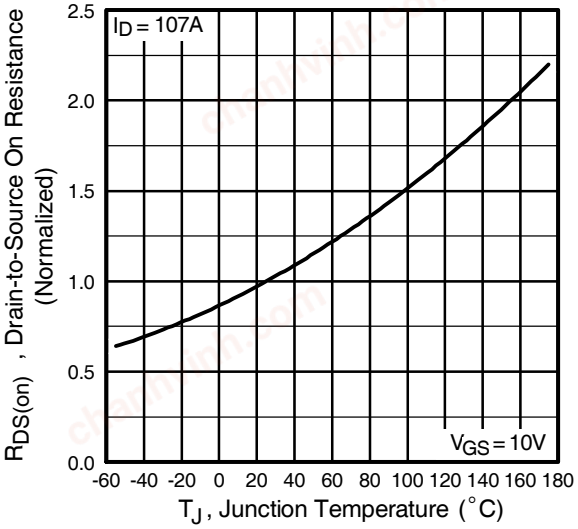


Fig 4. Normalized On-Resistance
Vs. Temperature

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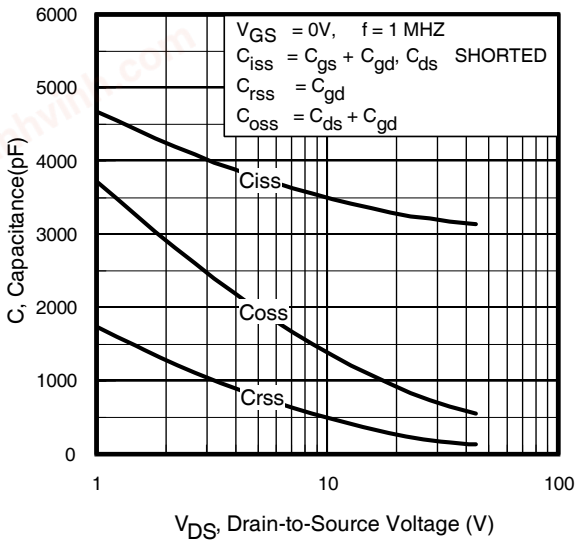


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

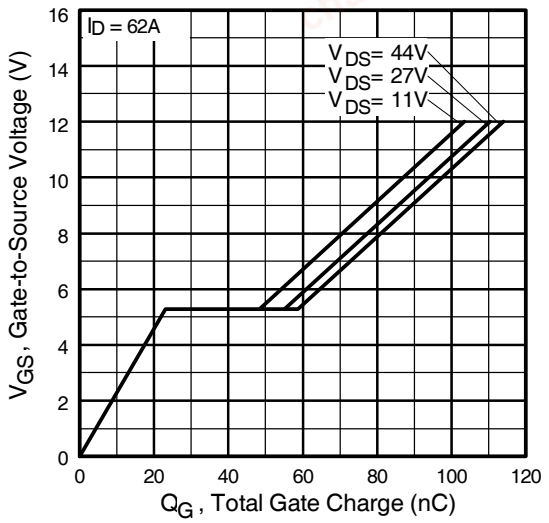


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

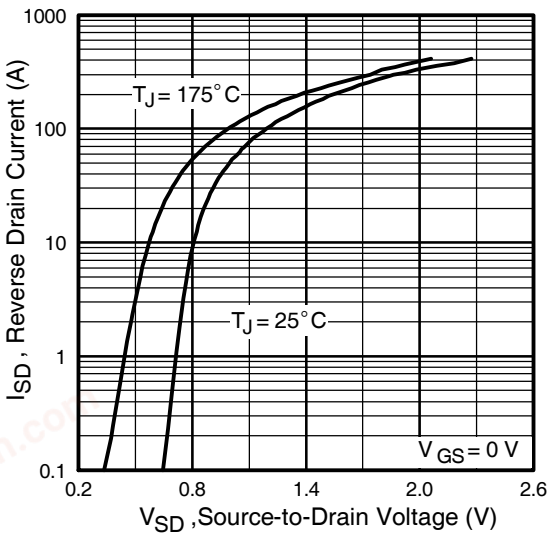


Fig 7. Typical Source-Drain Diode Forward Voltage

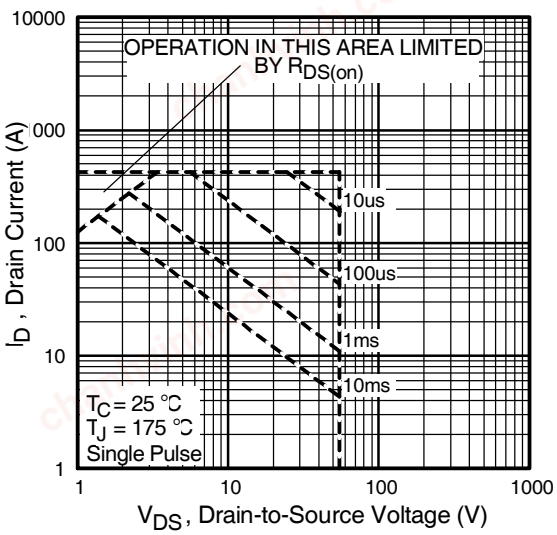


Fig 8. Maximum Safe Operating Area

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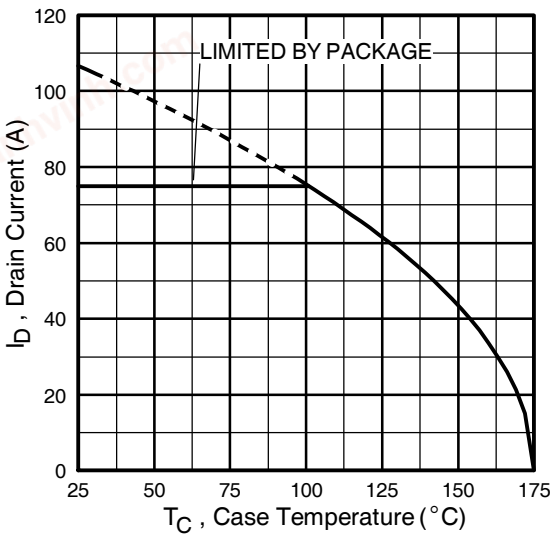


Fig 9. Maximum Drain Current Vs. Case Temperature

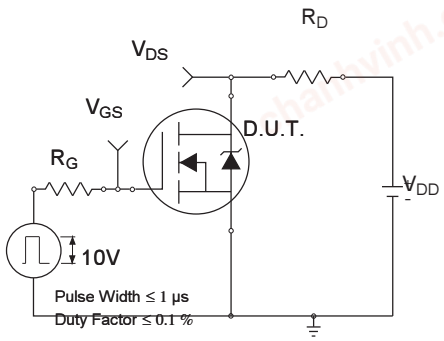


Fig 10a. Switching Time Test Circuit

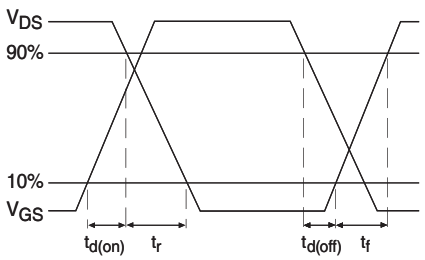


Fig 10b. Switching Time Waveforms

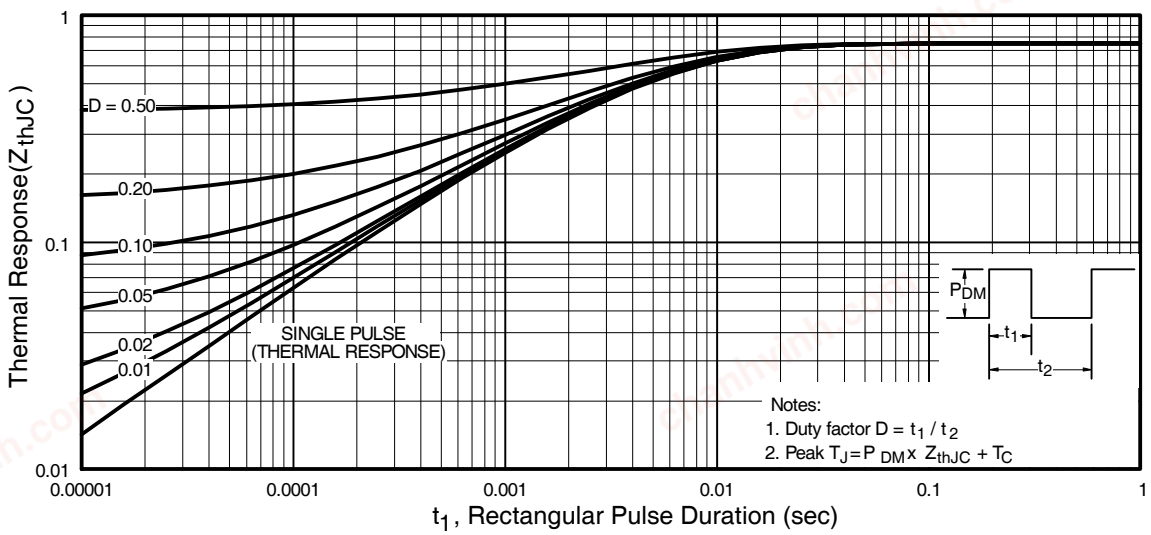


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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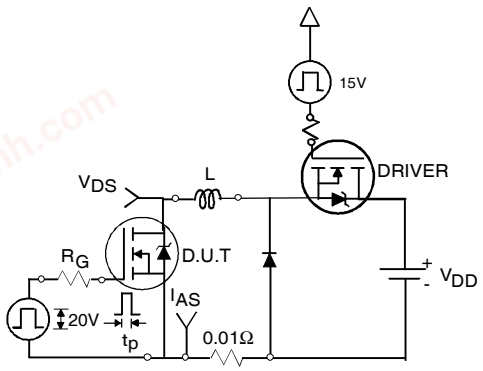


Fig 12a. Unclamped Inductive Test Circuit

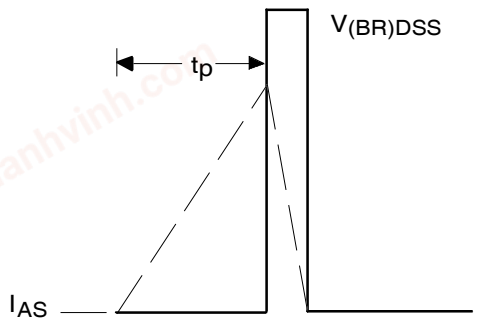


Fig 12b. Unclamped Inductive Waveforms

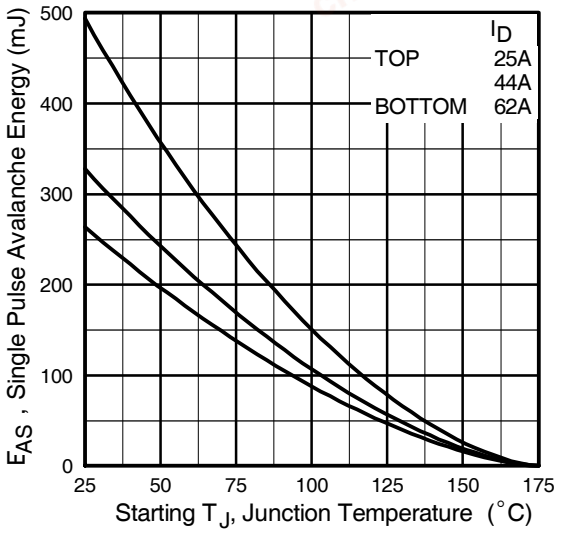


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

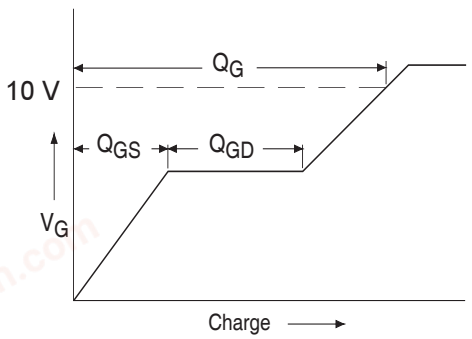


Fig 13a. Basic Gate Charge Waveform

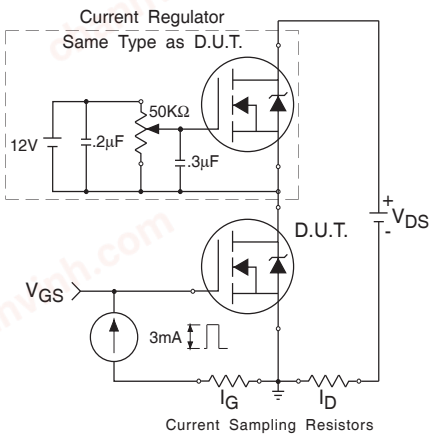
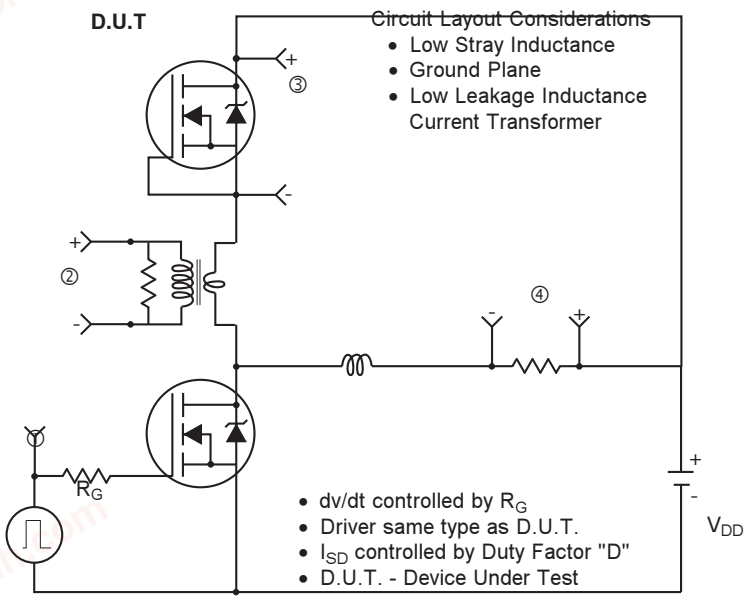
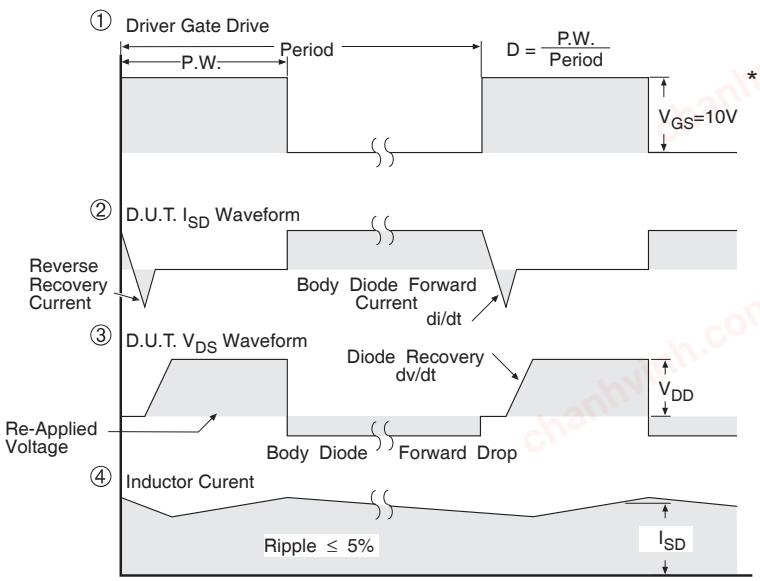


Fig 13b. Gate Charge Test Circuit

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Peak Diode Recovery dv/dt Test Circuit





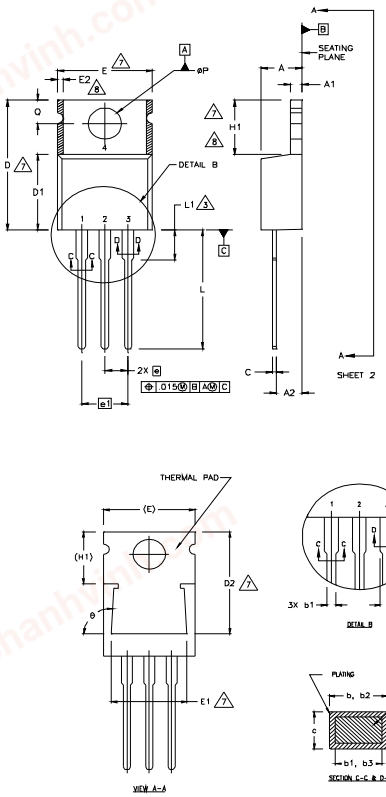
* V_{GS} = 5V for Logic Level Devices

Fig 14. For N-Channel HEXFETS

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TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M– 1994.
2 DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
3 LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
4 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5 DIMENSION b1 & c1 APPLY TO BASE METAL ONLY.
6 CONTROLLING DIMENSION : INCHES.
7 THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1
8 DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.

LEAD ASSIGNMENTS

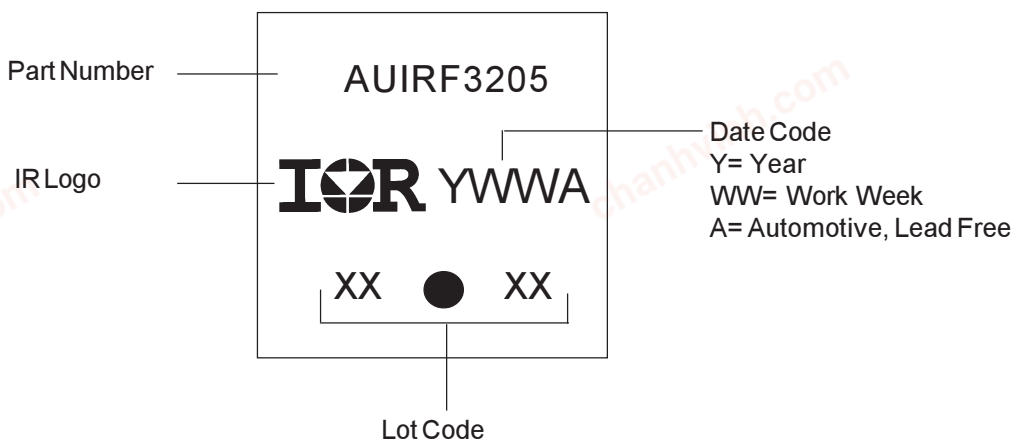
HEXFET
1.– GATE
2.– DRAIN
3.– SOURCE

IGBTs, CoPACK
1.– GATE
2.– COLLECTOR
3.– EMITTER

DIODES
1.– ANODE/OPEN
2.– CATHODE
3.– ANODE

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.82	.140	.190	
A1	0.51	1.40	.020	.055	
A2	2.04	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.96	.015	.038	5
b2	1.15	1.77	.045	.070	
b3	1.15	1.73	.045	.068	
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	5
D	14.22	16.51	.560	.650	4
D1	8.38	9.02	.330	.355	
D2	12.19	12.88	.480	.507	7
E	9.66	10.66	.380	.420	4,7
E1	8.38	8.89	.330	.350	7
e	2.54 BSC		.100 BSC		
e1	5.08		.200 BSC		
H1	5.85	6.55	.230	.270	7,8
L	12.70	14.73	.500	.580	
L1	–	6.35	–	.250	3
øP	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	
ø	90°–93°		90°–93°		

TO-220AB Part Marking Information



Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

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Ordering Information

Base part number	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRF3205	TO-220	Tube	50	AUIRF3205

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IMPORTANT NOTICE

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IR warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with IR's standard warranty. Testing and other quality control techniques are used to the extent IR deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

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For technical support, please contact IR's Technical Assistance Center
http://www.irf.com/technical-info/

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